优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

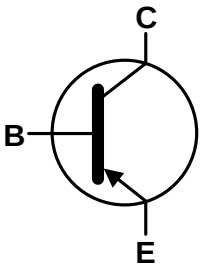
- BV_{CEO} > -40V
- I_C = -200mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: NK-MMST3904

Mechanical Data

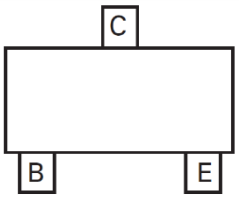
- Case: SOT323
- Case Material: Molded Plastic. “Green” Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT323

Top View



Device Symbol



Pin-out Top View

Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-200	mA

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

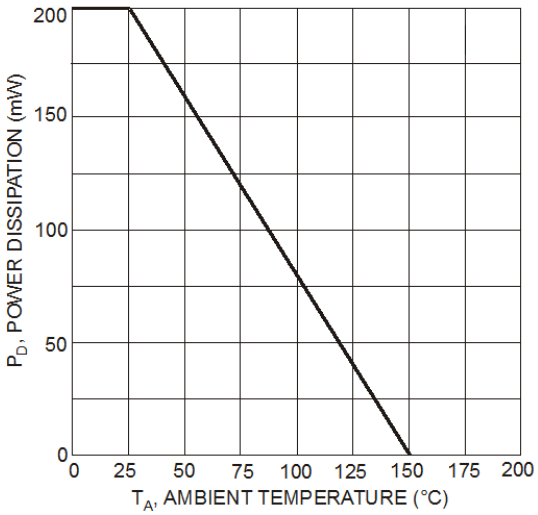


Fig. 1 Max Power Dissipation vs. Ambient Temperature

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					
Collector-Base Breakdown Voltage	BV_{CBO}	-40	—	V	I_C = -10μA, I_E = 0
Collector-Emitter Breakdown Voltage	BV_{CEO}	-40	—	V	I_C = -1mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	V	I_E = -10μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3V
Base Cutoff Current	I_{BL}	—	-50	nA	V_{CE} = -30V, $V_{EB(OFF)}$ = -3V
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h_{FE}	60 80 100 60 30	— — 300 — —	—	I_C = -100μA, V_{CE} = -1V I_C = -1mA, V_{CE} = -1V I_C = -10mA, V_{CE} = -1V I_C = -50mA, V_{CE} = -1V I_C = -100mA, V_{CE} = -1V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	-0.20 -0.30	V	I_C = -10mA, I_B = -1mA I_C = -50mA, I_B = -5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.65 —	-0.85 -0.95	V	I_C = -10mA, I_B = -1mA I_C = -50mA, I_B = -5mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	—	4.5	pF	V_{CB} = -5V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{IBO}	—	10	pF	V_{EB} = -0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{IE}	2	12	kΩ	V_{CE} = 1V, I_C = 10mA, f = 1kHz
Voltage Feedback Ratio	h_{RE}	0.1	10	x 10^{-4}	
Small Signal Current Gain	H_{FE}	100	400	—	
Output Admittance	h_{OE}	3	60	μS	
Current Gain-Bandwidth Product	f_T	300	—	MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz
Noise Figure	NF	—	4	dB	V_{CE} = -5V, I_C = -100μA, R_S = 1kΩ, f = 1kHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	35	ns	V_{CC} = -3V, I_C = -10mA, I_{B1} = -1mA, $V_{BE(off)}$ = 0.5V
Rise Time	t_r	—	35	ns	
Storage Time	t_s	—	225	ns	V_{CC} = -3V, I_C = -10mA, I_{B1} = I_{B2} = -1mA
Fall Time	t_f	—	75	ns	

Note: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

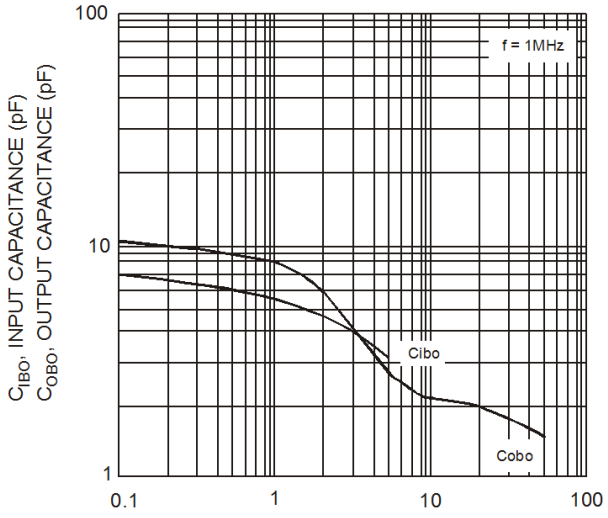


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

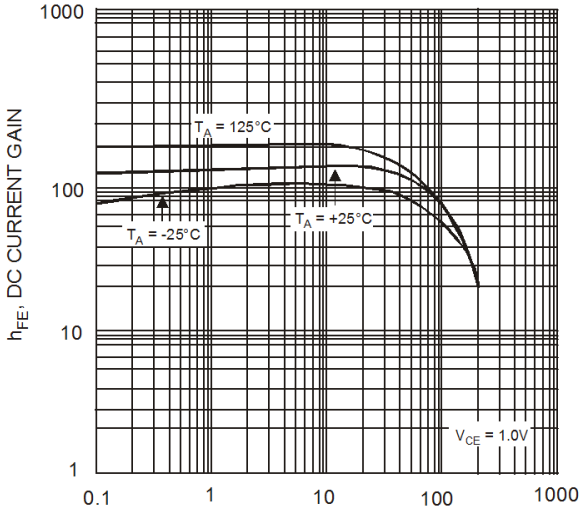


Fig. 3, Typical DC Current Gain vs Collector Current

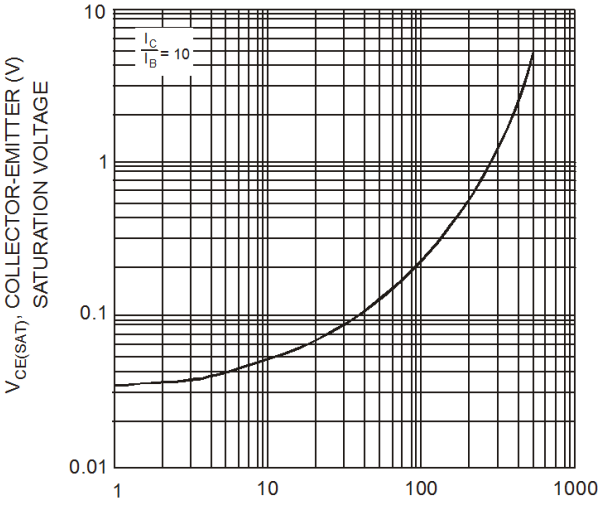


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

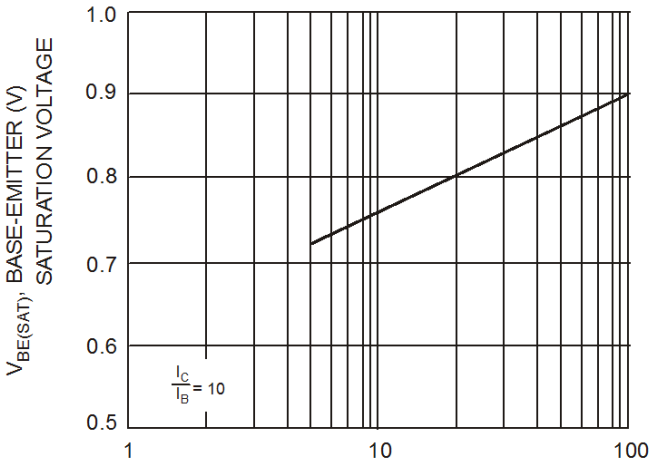
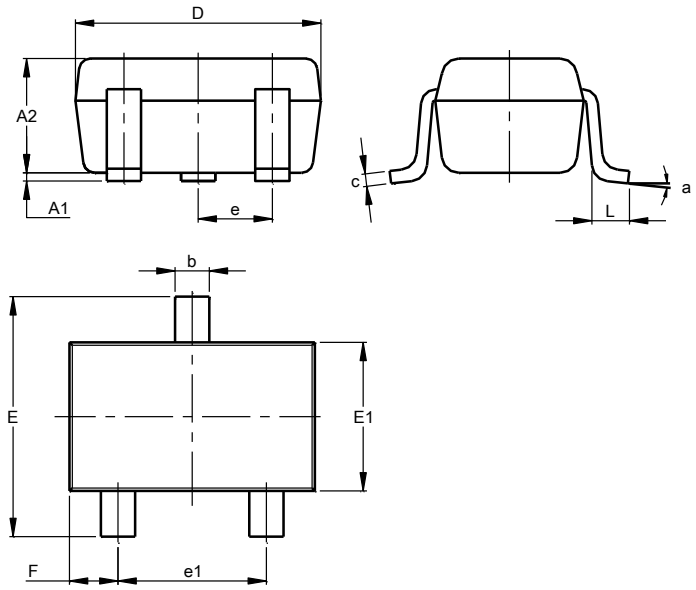


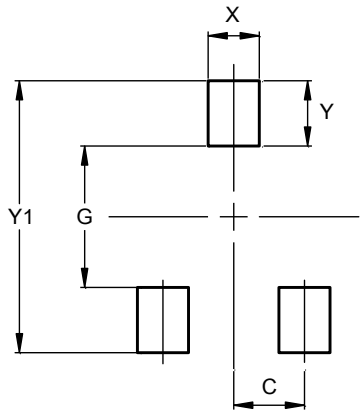
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Package Outline Dimensions



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500